

KTC3227 TRANSISTOR (NPN)

FEATURES

Power dissipation

$$P_{CM}: 1 \text{ W (Tamb=25}^\circ\text{C)}$$

Collector current

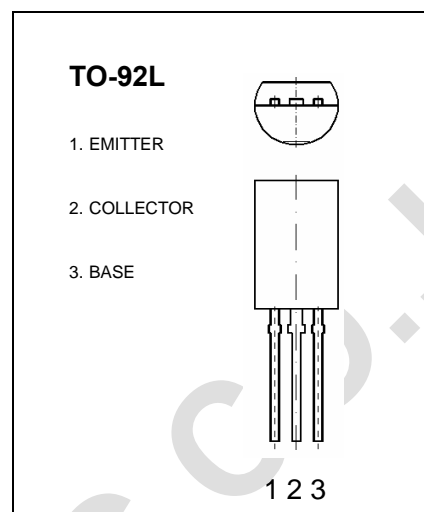
$$I_{CM}: 400 \text{ mA}$$

Collector-base voltage

$$V_{(BR)CBO}: 80 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55^\circ\text{C to } +150^\circ\text{C}$$



ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 1 \text{ mA}, I_E = 0$	80			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 5 \text{ mA}, I_B = 0$	80			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 1 \text{ mA}, I_C = 0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB} = 50 \text{ V}, I_E = 0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5 \text{ V}, I_C = 0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = 2 \text{ V}, I_C = 50 \text{ mA}$	70		240	
	$h_{FE(2)}$	$V_{CE} = 2 \text{ V}, I_C = 200 \text{ mA}$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 200 \text{ mA}, I_B = 20 \text{ mA}$			0.4	V
Base-emitter voltage	V_{BE}	$V_{CE} = 2 \text{ V}, I_C = 5 \text{ mA}$	0.55		0.8	V
Transition frequency	f_T	$V_{CE} = 10 \text{ V}, I_C = 10 \text{ mA}$		80		MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		10		pF

CLASSIFICATION OF h_{FE}

Rank	O	Y
Range	70-140	120-240